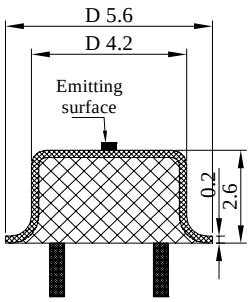
InAsSbP photodiode — PD27fs mIL

Peak wavelength	λ	μm	2.7±0.1
Spectral response range	$\lambda_{0.1}$	μm	1.15÷3.15
Current sensitivity	S_I	A/W	0.5÷0.6
Resistance at zero bias	R_0	Ohm	≥400
Detectivity	$D^*_{\lambda_{max}}$	$cmHz^{1/2}W^{-1}$	$\geq 1\times10^{10}$
Voltage sensitivity	S_U	V/W	≥400
Switching time	τ	ns	<20

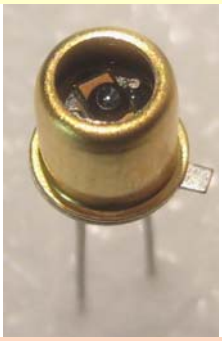
Model	Package	Lens material; Cap with window	Sensitive area, mm	Angle of view FWHM, deg.	Operation conditions, °C	Polarity
PD27fs mILTO18	TO18	Chalcogenide glass	∅1.0	≥60	-25÷+60	Leg near key is negative
PD27fs mILTO18c	TO18	Chalcogenide glass; Sapphire		50		

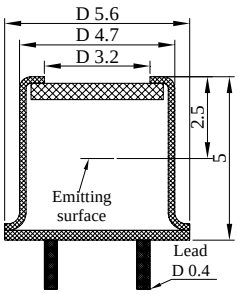
Product view

PD27fs mILTO18



PD27fs mILTO18c





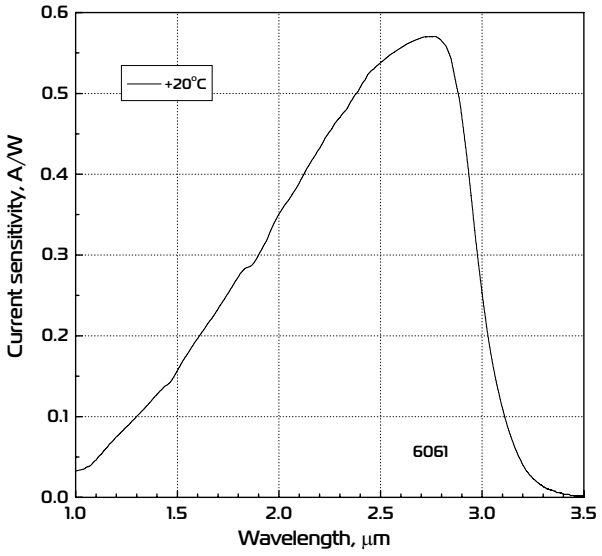
Features

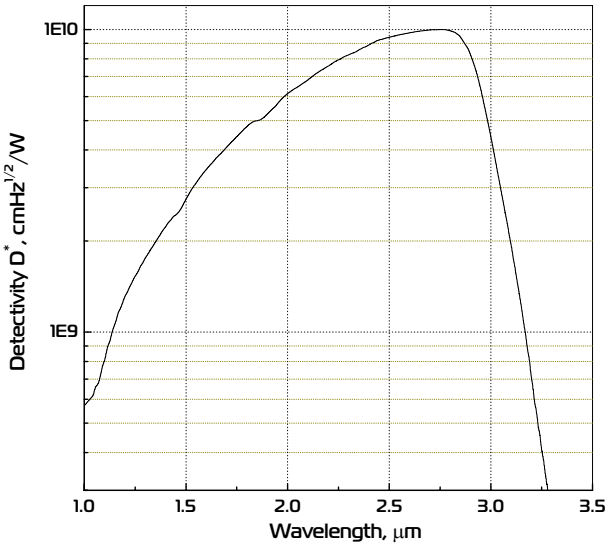
Growth of narrow gap semiconductor alloys onto n^+-InAs substrate; "Wide gap" window; Optical coupling through the use of chalcogenide glass lenses

Ambient and high temperature operation; No bias required; Short time constant; High value of shunt resistance; Operation from DC to VHF; Highest long term stability

Data are valid for 22°C. Photodiode could be equipped with preamplifier that is designed for conversion of PD photocurrent into a convenient output voltage and is adjusted for the particular PD taking into account the Ro value and frequency range. Other packages are available upon request

Spectral response and shunt resistance vs. temperature





Product specifications are subject to change without prior notice due to improvements or other reasons. Updated 26.11.12

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